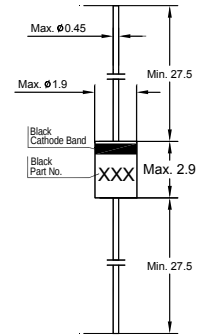


ZS Series

Silicon Epitaxial Planar Zener Diodes



Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	500 ¹⁾	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^\circ\text{C}$

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 8 mm from case.

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient Air	R_{thA}	0.3 ¹⁾	K/mW
Forward Voltage at $I_F = 100\text{ mA}$	V_F	1	V

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 8 mm from case.

Characteristics at $T_a = 25^\circ\text{C}$

Type	Zener Voltage ¹⁾			Dynamic Resistance		Reverse Leakage Current	
	V_Z		at I_{ZT}	Z_{ZT}	at I_{ZT}	I_R	at V_R
	Min. (V)	Max. (V)	(mA)	Max. (Ω)	(mA)	Max. (μA)	(V)
ZS3C-1	3.1	3.3	5	100	5	5	0.5
ZS3C-2	3.2	3.4	5	100	5	5	0.5
ZS3C-3	3.3	3.5	5	100	5	5	0.5
ZS33-1	31.2	32.6	2	120	2	1	25
ZS33-2	32.2	33.6	2	120	2	1	25
ZS33-3	33.2	34.6	2	120	2	1	25

¹⁾ Tested with pulses $t_p = 20\text{ ms}$.

